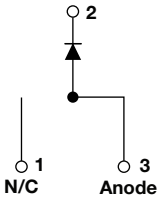
HEXFRED®, Ultrafast Soft Recovery Diode, 4 A

TO-263AB (D^2PAK)



FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT HALOGEN FREE

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

PRODUCT SUMMARY	
Package	TO-263AB (D^2PAK)
$I_{F(AV)}$	4 A
V_R	600 V
V_F at I_F	1.4 V
t_{rr} (typ.)	17 ns
T_J max.	150 °C
Diode variation	Single die

DESCRIPTION

VS-HFA04TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A continuous current, the VS-HFA04TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA04TB60S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V_R		600	V
Maximum continuous forward current	I_F	T_C = 100 °C	4	A
Single pulse forward current	I_{FSM}		25	
Maximum repetitive forward current	I_{FRM}		16	
Maximum power dissipation	P_D	T_C = 25 °C	25	W
		T_C = 100 °C	10	
Operating junction and storage temperature range	T_J, T_{Stg}		-55 to +150	°C

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Cathode to anode breakdown voltage	V_{BR}	I_R = 100 µA		600	-	-	V
Maximum forward voltage	V_{FM}	I_F = 4.0 A	See fig. 1	-	1.5	1.8	
		I_F = 8.0 A		-	1.8	2.2	
		I_F = 4.0 A, T_J = 125 °C		-	1.4	1.7	
Maximum reverse leakage current	I_{RM}	V_R = V_R rated	See fig. 2	-	0.17	3.0	µA
		T_J = 125 °C, V_R = 0.8 x V_R rated		-	44	300	
Junction capacitance	C_T	V_R = 200 V	See fig. 3	-	4.0	8.0	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body		-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Reverse recovery time See fig. 5, 6	t_{rr}	I_F = 1.0 A, dI_F/dt = 200 A/µs, V_R = 30 V		-	17	-	ns
	t_{rr1}	T_J = 25 °C	I_F = 4.0 A dI_F/dt = 200 A/µs V_R = 200 V	-	28	42	
	t_{rr2}	T_J = 125 °C		-	38	57	
Peak recovery current	I_{RRM1}	T_J = 25 °C		-	2.9	5.2	A
	I_{RRM2}	T_J = 125 °C		-	3.7	6.7	
Reverse recovery charge See fig. 7	Q_{rr1}	T_J = 25 °C		-	40	60	nC
	Q_{rr2}	T_J = 125 °C		-	70	105	
Peak rate of fall of recovery current during t_b See fig. 8	$dI_{(rec)M}/dt1$	T_J = 25 °C		-	280	-	A/µs
	$dI_{(rec)M}/dt2$	T_J = 125 °C		-	235	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Lead temperature	T_{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R_{thJC}		-	-	5.0	K/W
Thermal resistance, junction to ambient	R_{thJA}	Typical socket mount	-	-	80	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Marking device		Case style TO-263AB (D^2PAK)	HFA04TB60S			

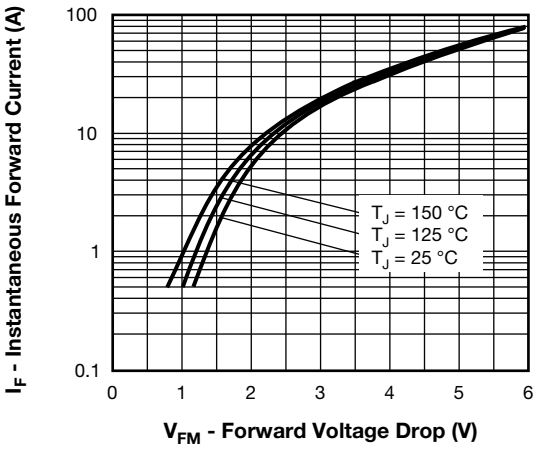


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

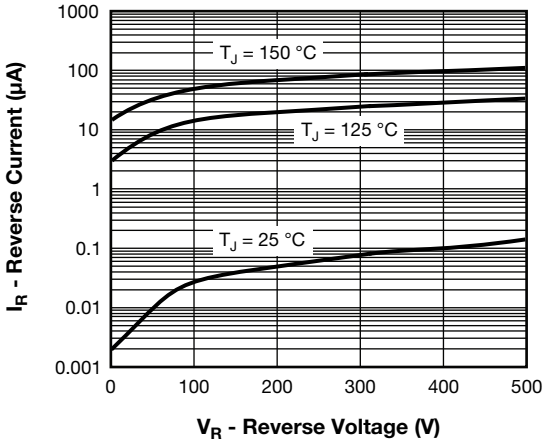


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

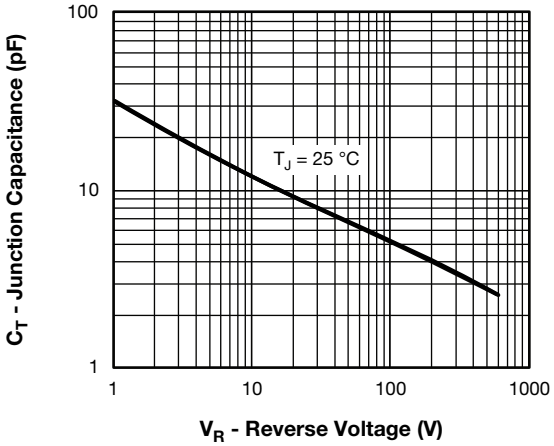


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

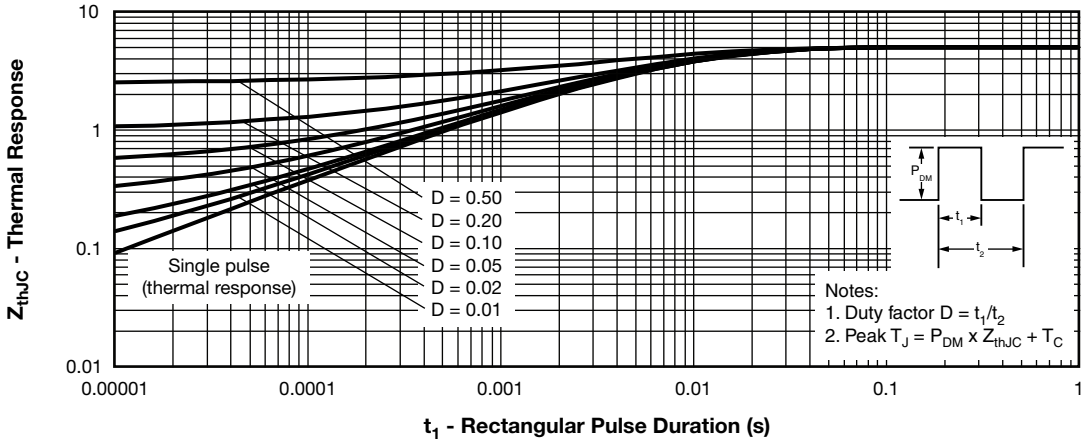


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

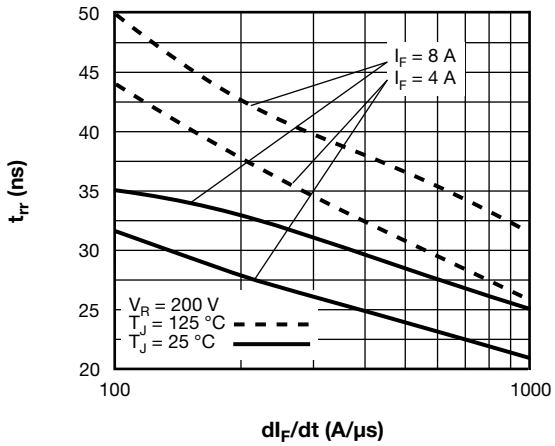


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

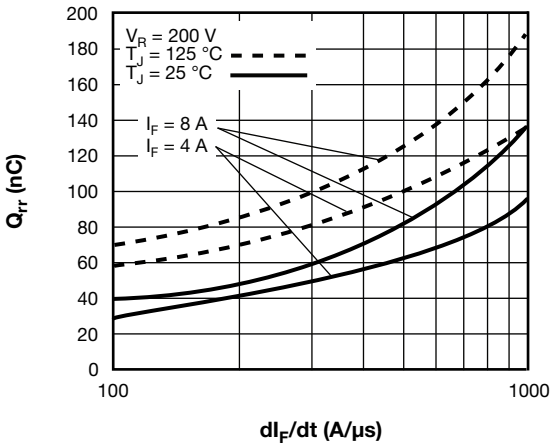


Fig. 7 - Typical Stored Charge vs. dI_F/dt

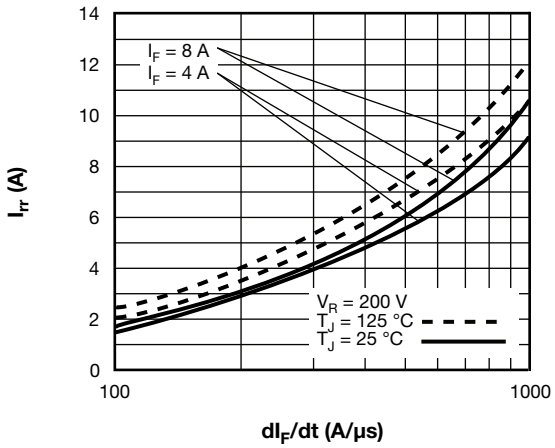


Fig. 6 - Typical Recovery Current vs. dI_F/dt

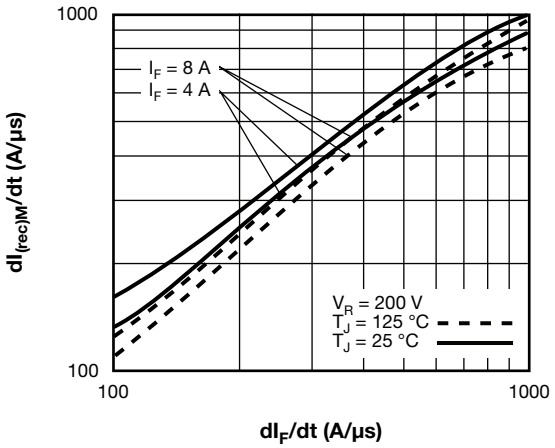


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

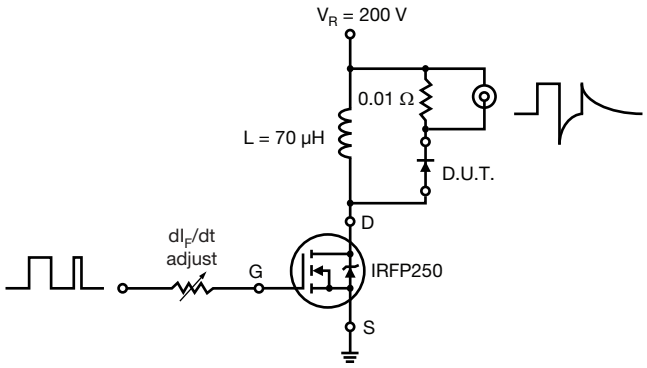
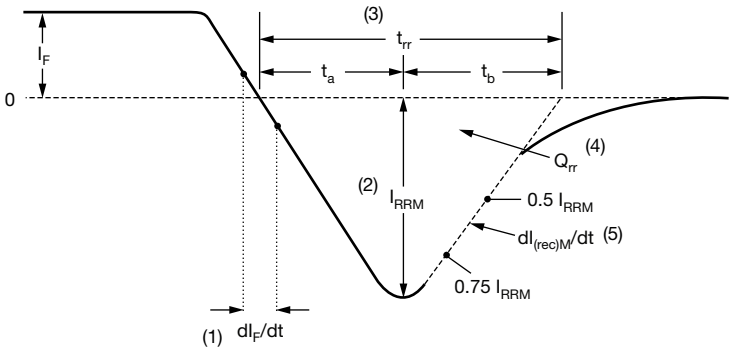


Fig. 9 - Reverse Recovery Parameter Test Circuit



(1) dI_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

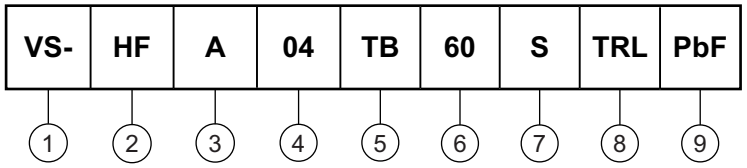
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



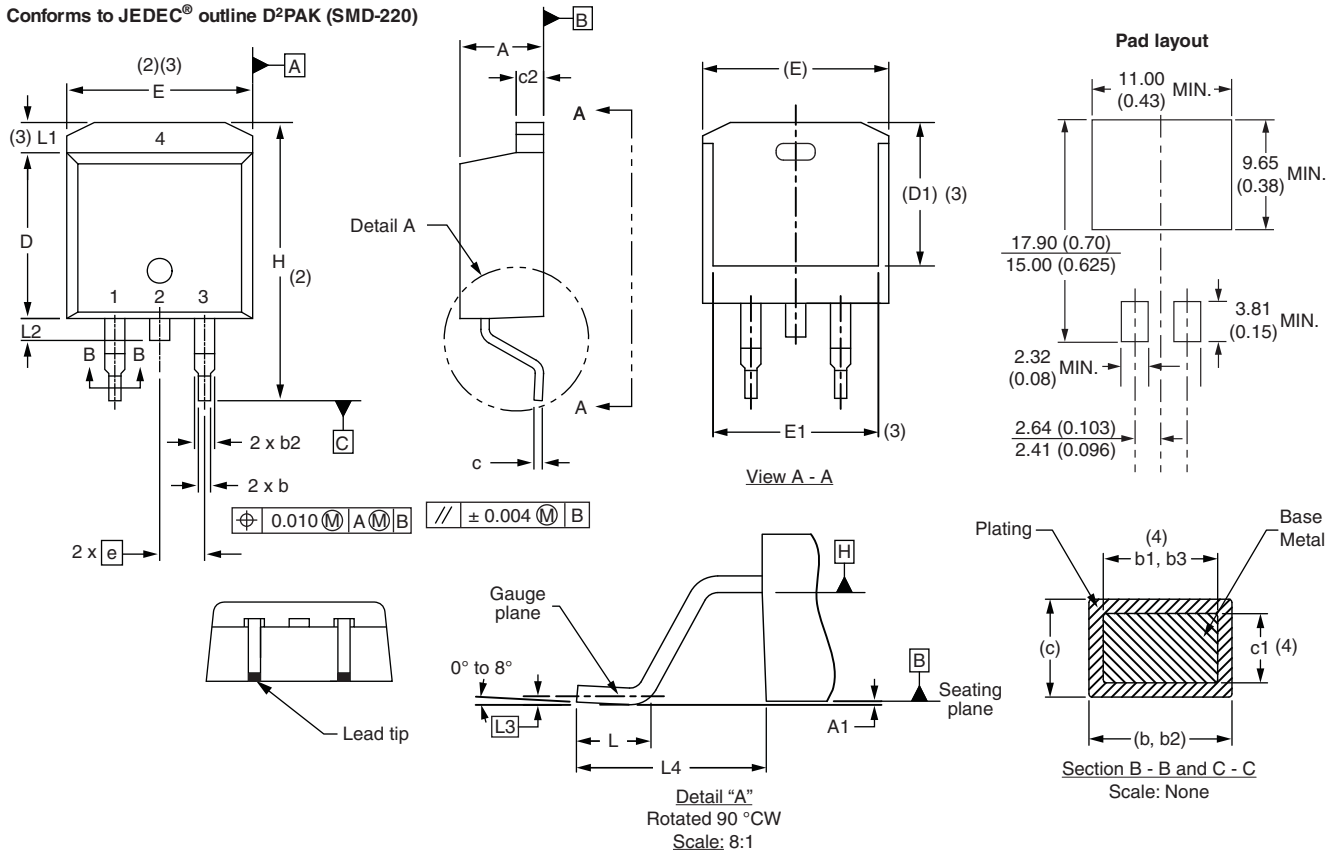
1 - Vishay Semiconductors product
2 - HEXFRED® family
3 - Process designator: A = electron irradiated
4 - Current rating (04 = 4 A)
5 - Package outline (TB = TO-220, 2 leads)
6 - Voltage rating (60 = 600 V)
7 - S = D^2PAK
8 - • None = tube (50 pieces)
• TRL = tape and reel (left oriented)
• TRR = tape and reel (right oriented)
9 - • PbF = lead (Pb)-free, for tube packaged
• P = lead (Pb)-free, for tape and reel packaged

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER TUBE OR TAPE AND REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-HFA04TB60SPBF	50	1000	Antistatic plastic tube
VS-HFA04TB60STRLP	800	800	13" diameter reel
VS-HFA04TB60STRRP	800	800	13" diameter reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95046
Part marking information	www.vishay.com/doc?95054
Packaging information	www.vishay.com/doc?95032

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

(1) Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

(4) Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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